

Description

The IRFR120NTRPBF uses advanced trench technology and

design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

 $V_{DS} = 100V, I_D = 10A$ $R_{DS(ON)} < 160m\Omega @ V_{GS} = 10V$

 $R_{DS(ON)}$ <170m Ω @ V_{GS}=4.5V

High density cell design for ultra low Rdson

Fully characterized avalanche voltage and current

Excellent package for good heat dissipation

Application

Power switching application

Hard switched and high frequency circuits

Uninterruptible power supply

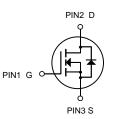
Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRFR120NTRPBF	TO252-2L	10N10 XXYY	2500

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	100	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	ID	10	A	
Drain Current-Pulsed (Note 1)	Ідм	20	A	
Maximum Power Dissipation	PD	40	W	
Operating Junction and Storage Temperature Range	Тј,Тѕтб	-55 To 175	°C	
Thermal Resistance, Junction-to-Case (Note 2)	Rejc	3.75	°C/W	





N-Channel MOSFET



IRFR120NTRPBF

N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V I _D =250µA	100	-	-	V	
Zero Gate Voltage Drain Current	loss	V _{DS} =100V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	lgss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA	
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =250µA	1.0		2.5	V	
		V _{GS} =10V, I _D =3A	-	140	160	mΩ	
Drain-Source On-State Resistance	Rds(on)	V_{GS} =4.5V, I _D =3A	-	160	170		
Forward Transconductance	gfs	V _{DS} =5V,I _D =3A	-	5	-	S	
Input Capacitance	Clss		-	650	-	PF	
Output Capacitance	Coss	V_{DS} =50V, V_{GS} =0V,	-	25	-	PF	
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	20	-	PF	
Turn-on Delay Time	td(on)		-	6	-	nS	
Turn-on Rise Time	tr	V_{DD} =50V, RL=19 Ω	-	4	-	nS	
Turn-Off Delay Time	td(off)	V_{GS} =10V,R _G =3 Ω	-	20	-	nS	
Turn-Off Fall Time	tr		-	4	-	nS	
Total Gate Charge	Qg		-	20.6		nC	
Gate-Source Charge	Qgs	V_{DS} =50V,I _D =3A,	-	2.1	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	3.3	-	nC	
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =3A	-	-	1.2	V	
Diode Forward Current (Note 2)	ls		-	-	7	Α	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

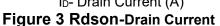
3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

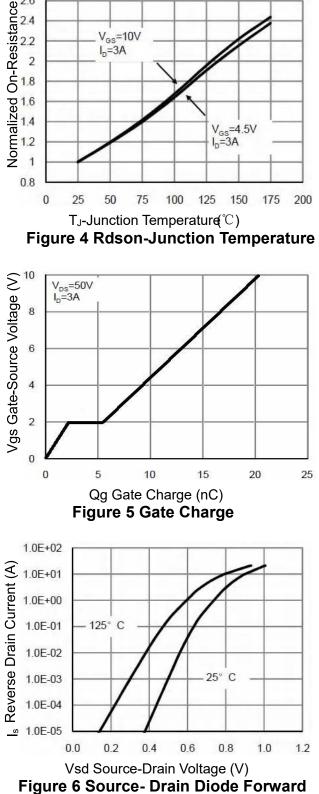
4. Guaranteed by design, not subject to production



20 Normalized On-Resistance Normalized On-Resistance Normalized On-Resistance Normalized On-Resistance 10V 3.5V 15 Drain Current (A) 2 5V 10 2V 5 V_{GS}=1.5V 0.8 0 0 25 2 3 4 5 0 1 Vds Drain-Source Voltage (V) **Figure 1 Output Characteristics** 20 10 Vgs Gate-Source Voltage (V) V_{DS}=5V V_{DS}=50V I_D Drain Current (A) I ID=3A 8 15 6 10 4 125° C 5 2 25° C 0 0 0 2 3 5 1 4 0 Vgs Gate-Source Voltage (V) **Figure 2 Transfer Characteristics** 1.0E+02 160 Rdson On-Resistance⁽²⁾ Reverse Drain Current (A) 1.0E+01 V_{GS}=4.5V 150 1.0E+00 1.0E-01 140 1.0E-02 1.0E-03 130 V_{gs}=10V 1.0E-04 120 S 1.0E-05 0 2 4 6 8 0.0 ID- Drain Current (A)

Typical Electrical and Thermal Characteristics (Curves)

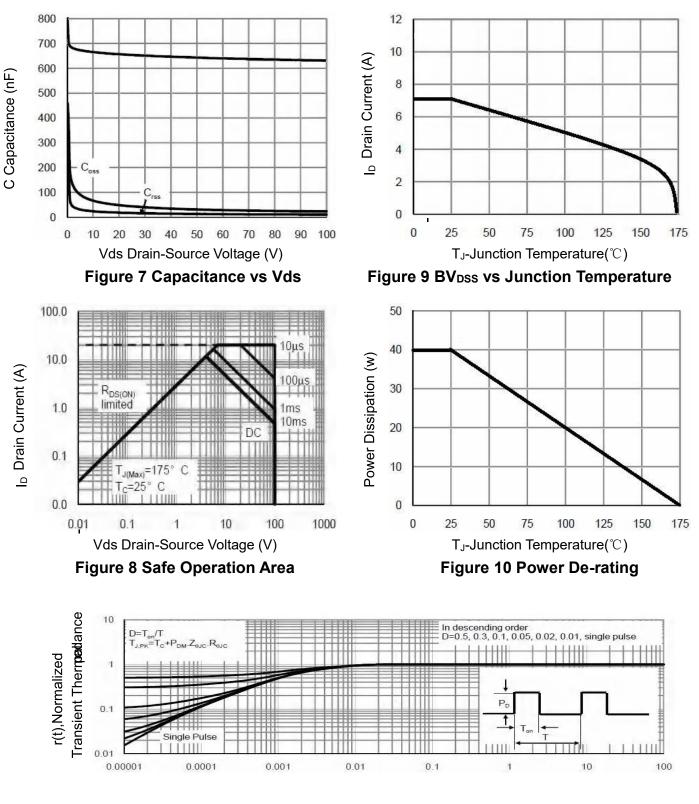






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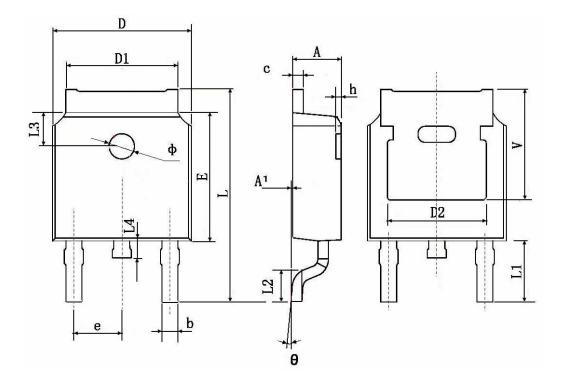


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient' Thermal Impedance



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
с	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	0.483	0.483 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600	TYP.	0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Φ	1.100	1.300	0.043	0.051		
θ	0°	8°	0 °	8°		
h	0.000	0.300	0.000	0.012		
V	5.350) TYP.	0.211 TYP.			



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